Richard J Potter

List of Publications by Year
in descending order

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67	1,630	236833 25	315616 38
papers	citations	h-index	g-index

68	68	68	2347
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Comparison of atomic layer deposited Al2O3 and (Ta2O5)0.12(Al2O3)0.88 gate dielectrics on the characteristics of GaN-capped AlGaN/GaN metal-oxide-semiconductor high electron mobility transistors. Journal of Applied Physics, 2019, 126, .	1.1	9
2	Band Alignments, Band Gap, Core Levels, and Valence Band States in Cu₃BiS₃ for Photovoltaics. ACS Applied Materials & Interfaces, 2019, 11, 27033-27047.	4.0	37
3	Elucidation of ALD MgZnO deposition processes using low energy ion scattering. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, .	0.9	5
4	Directing the mechanism of CO₂ reduction by a Mn catalyst through surface immobilization. Physical Chemistry Chemical Physics, 2018, 20, 6811-6816.	1.3	26
5	Stable Ta₂O₅ Overlayers on Hematite for Enhanced Photoelectrochemical Water Splitting Efficiencies. ChemPhotoChem, 2018, 2, 183-189.	1.5	15
6	The influence of tertiary butyl hydrazine as a co-reactant on the atomic layer deposition of silver. Applied Surface Science, 2017, 399, 123-131.	3.1	18
7	Atomic Layer Deposition of a Silver Nanolayer on Advanced Titanium Orthopedic Implants Inhibits Bacterial Colonization and Supports Vascularized de Novo Bone Ingrowth. Advanced Healthcare Materials, 2017, 6, 1700033.	3.9	35
8	The role of nitrogen doping in ALD Ta2O5 and its influence on multilevel cell switching in RRAM. Applied Physics Letters, 2017, 110, .	1.5	54
9	Enhanced switching stability in Ta2O5 resistive RAM by fluorine doping. Applied Physics Letters, 2017, 111, .	1.5	21
10	Core Levels, Band Alignments, and Valence-Band States in CuSbS₂ for Solar Cell Applications. ACS Applied Materials & Interfaces, 2017, 9, 41916-41926.	4.0	67
11	Biotransformation of Silver Released from Nanoparticle Coated Titanium Implants Revealed in Regenerating Bone. ACS Applied Materials & Interfaces, 2017, 9, 21169-21180.	4.0	39
12	Comparative analysis of the effects of tantalum doping and annealing on atomic layer deposited (Ta2O5)x(Al2O3)1â^'x as potential gate dielectrics for GaN/AlxGa1â^'xN/GaN high electron mobility transistors. Journal of Applied Physics, 2016, 119, .	1.1	6
13	Self-limiting atomic layer deposition of conformal nanostructured silver films. Applied Surface Science, 2016, 364, 789-797.	3.1	25
14	The Effects of Zr Doping on the Optical, Electrical and Microstructural Properties of Thin ZnO Films Deposited by Atomic Layer Deposition. Materials, 2015, 8, 7230-7240.	1.3	43
15	(Invited) Vacuum Ultraviolet Photochemical Atomic Layer Deposition of Alumina and Titania Films. ECS Transactions, 2015, 69, 139-145.	0.3	3
16	Oxygen deficient Î±-Fe₂O₃ photoelectrodes: a balance between enhanced electrical properties and trap-mediated losses. Chemical Science, 2015, 6, 4009-4016.	3.7	92
17	Vacuum ultraviolet photochemical selective area atomic layer deposition of Al2O3 dielectrics. AIP Advances, 2015, 5, .	0.6	16
18	Tuning the electrical properties of ZnO thin-film transistors by thermal annealing in different gases. Thin Solid Films, 2014, 552, 192-195.	0.8	15

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19	Gadolinium nitride films deposited using a PEALD based process. Journal of Crystal Growth, 2012, 338, 111-117.	0.7	15
20	Polymer-nanoparticle composites composed of PEDOT:PSS and nanoparticles of Ag synthesised by laser ablation. Colloid and Polymer Science, 2012, 290, 213-220.	1.0	13
21	Atomic layer deposition of TaN and Ta3N5 using pentakis(dimethylamino)tantalum and either ammonia or monomethylhydrazine. Journal of Crystal Growth, 2011, 331, 33-39.	0.7	43
22	Picosecond laser patterning of PEDOT:PSS thin films. Synthetic Metals, 2011, 161, 431-439.	2.1	37
23	Silicon nanoparticles generated by femtosecond laser ablation in a liquid environment. Journal of Nanoparticle Research, 2010, 12, 573-580.	0.8	71
24	Modification of the electrical properties of PEDOT:PSS by the incorporation of ZnO nanoparticles synthesized by laser ablation. Chemical Physics Letters, 2010, 484, 283-289.	1.2	58
25	IIâ€“VI semiconductor nanoparticles synthesized by laser ablation. Applied Physics A: Materials Science and Processing, 2009, 94, 641-647.	1.1	50
26	CdTe nanoparticles synthesized by laser ablation. Applied Physics Letters, 2009, 95, .	1.5	26
27	High-k materials and their response to gamma ray radiation. Journal of Vacuum Science & Technology B, 2009, 27, 411.	1.3	27
28	CdSe nanoparticles synthesized by laser ablation. Europhysics Letters, 2008, 84, 47001.	0.7	27
29	Permittivity enhancement of hafnium dioxide high-Îº films by cerium doping. Applied Physics Letters, 2008, 93, .	1.5	67
30	The Effects of Nitrogen Incorporation on Photogenerated Carrier Dynamics in Dilute Nitrides. , 2008, , 181-197.		1
31	Deposition of Pr- and Nd-aluminate by Liquid Injection MOCVD and ALD Using Single-Source Heterometallic Alkoxide Precursors. Chemistry of Materials, 2007, 19, 4796-4803.	3.2	20
32	Charge trapping and interface states in hydrogen annealed HfO2â€“Si structures. Microelectronics Reliability, 2007, 47, 714-717.	0.9	1
33	Tuneable electrical properties of hafnium aluminate gate dielectrics deposited by metal organic chemical vapour deposition. Microelectronics Reliability, 2007, 47, 722-725.	0.9	8
34	Investigation of optical and electronic properties of hafnium aluminate films deposited by Metalâ€“Organic Chemical Vapour Deposition. Thin Solid Films, 2007, 515, 3772-3778.	0.8	19
35	Optical and electrical characterization of hafnium oxide deposited by liquid injection atomic layer deposition. Microelectronics Reliability, 2007, 47, 825-829.	0.9	10
36	Charge trapping characterization of MOCVD HfO2/p-Si interfaces at cryogenic temperatures. Microelectronics Reliability, 2007, 47, 726-728.	0.9	6

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37	Spectroellipsometric assessment of HfO2 thin films. Thin Solid Films, 2006, 515, 623-626.	0.8	28
38	Recent developments in the MOCVD and ALD of rare earth oxides and silicates. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2005, 118, 97-104.	1.7	56
39	Deposition of HfO2, Gd2O3 and PrOx by Liquid Injection ALD Techniques. Chemical Vapor Deposition, 2005, 11, 159-169.	1.4	61
40	Deposition of HfO2 Films by Liquid Injection MOCVD Using a New Monomeric Alkoxide Precursor, [Hf(dmop)4]. Chemical Vapor Deposition, 2005, 11, 299-305.	1.4	14
41	A superlattice approach to the synthesis of ferroelectric Strontium Bismuth Tantalate thin films using liquid-injection-MOCVD. Materials Research Society Symposia Proceedings, 2005, 902, 1.	0.1	0
42	Deposition of HfO2 and ZrO2 films by liquid injection MOCVD using new monomeric alkoxide precursors. Journal of Materials Chemistry, 2005, 15, 1896.	6.7	33
43	Characterization of hafnium aluminate gate dielectrics deposited by liquid injection metalorganic chemical vapor deposition. Applied Physics Letters, 2004, 84, 4119-4121.	1.5	21
44	Thermal stability of hafnium silicate dielectric films deposited by a dual source liquid injection MOCVD. Journal of Materials Science: Materials in Electronics, 2004, 15, 711-714.	1.1	3
45	Atomic vapour deposition (AVD) of SrBi2Ta2O9 using an all alkoxide precursor. Journal of Crystal Growth, 2004, 272, 778-784.	0.7	8
46	Growth of Hafnium Aluminate Thin Films by Liquid Injection MOCVD Using Alkoxide Precursors. Chemical Vapor Deposition, 2004, 10, 275-279.	1.4	16
47	Growth of Neodymium Oxide This Films by Liquid Injection MOCVD Using a New Neodymium Alkoxide Precursor. Chemical Vapor Deposition, 2004, 10, 301-305.	1.4	23
48	Growth of Gadolinium Oxide This Films by Liquid Injection MOCVD Using a New Gadolinium Alkoxide Precursor. Chemical Vapor Deposition, 2004, 10, 306-310.	1.4	18
49	Synthesis and characterisation of four new heterometal alkoxides: potential precursors for the MOCVD of ferroelectric oxides. Journal of Materials Chemistry, 2004, 14, 887.	6.7	12
50	Some recent developments in the MOCVD and ALD of high-Î° dielectric oxides. Journal of Materials Chemistry, 2004, 14, 3101-3112.	6.7	78
51	Optical properties of GaNAs and GaInAsN quantum wells. Journal of Physics Condensed Matter, 2004, 16, S3387-S3412.	0.7	56
52	Optical properties of GaInNAs/GaAs quantum wells. Solid-State Electronics, 2003, 47, 483-487.	0.8	8
53	Comparison of theoretical models for interband transitions in dilute nitrides and experimental measurement. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 240-241.	1.3	2
54	S-shaped behaviour of the temperature-dependent energy band gap in dilute nitrides. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 242-244.	1.3	34

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55	Band structure and optical gain in GaInAsN quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 245-246.	1.3	7
56	Photo-induced transient spectroscopy and in-plane photovoltage in GaInNAs/GaAs quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 250-251.	1.3	1
57	Hot electron light emission from GaInAsP/InP structures with distributed Bragg reflectors. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 607-609.	1.3	3
58	The operation of a wavelength converter basedon a field effect light emitting and absorbing heterojunction. Physica Status Solidi A, 2003, 196, 496-503.	1.7	3
59	Effect of nitrogen fraction on the temperature dependence of GaNAs/GaAs quantum-well emission. Applied Physics Letters, 2003, 82, 3400-3402.	1.5	12
60	In-plane photovoltage and photoluminescence studies in sequentially grown GaInNAs and GaInAs quantum wells. Journal of Applied Physics, 2003, 93, 2440-2448.	1.1	14
61	The effect of In/N ratio on the optical quality and lasing threshold in GaxIn1âˆ'xAs1âˆ'yNy/GaAs laser structures. Superlattices and Microstructures, 2001, 29, 169-186.	1.4	23
62	Interaction Strength between the Highly Localised Nitrogen States and the Extended Semiconductor Matrix States in GaInNAs. Physica Status Solidi A, 2001, 187, 623-632.	1.7	37
63	Compositional variation in as-grown GaInNAs/GaAs quantum well structures. Journal of Crystal Growth, 2001, 233, 1-4.	0.7	21
64	Optical characterization of GaInNAs. , 2001, 4283, 638.		0
65	1.5-Î¼m surface emission from GaInAsP/InP HELLISH structures. , 2001, 4283, 723.		1
66	VCSEL structure hot electron light emitter. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 74, 96-100.	1.7	7
67	Operation of a novel hot-electron vertical-cavity surface-emitting laser. , 1998, , .		5